

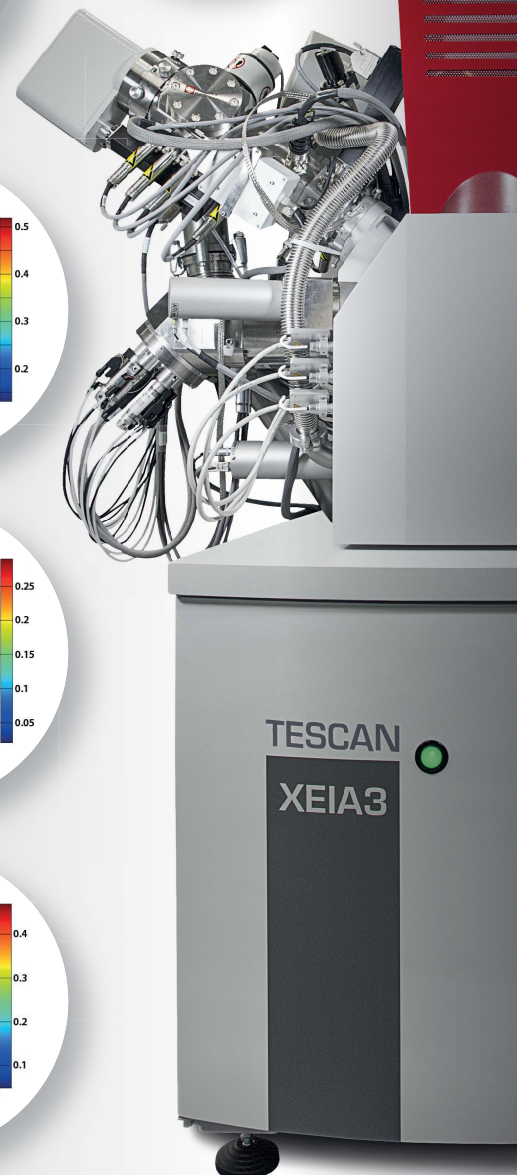
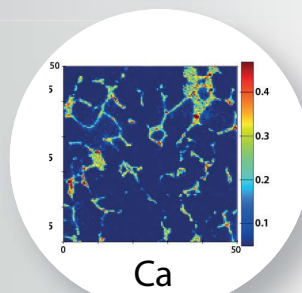
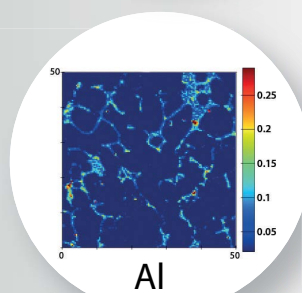
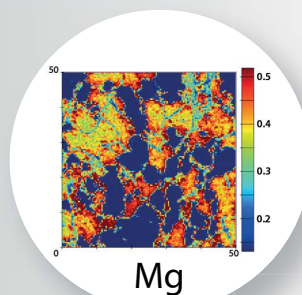
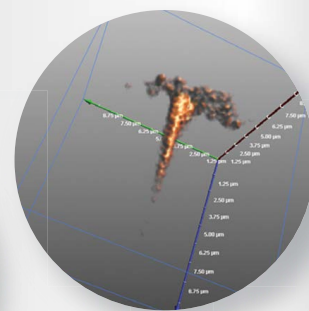
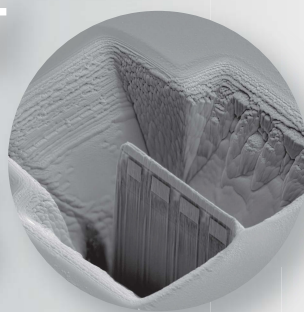
Increasing the Performance and Analytical Power of FIB-SEMs

Xe plasma FIBs or iFIBs offer extremely high material removal rates and very low contamination compared to conventional gallium FIBs. As such Xe plasma FIBs have great potential in applications such as failure analysis and MEMS fabrication in the semiconductor industry as well as in generating large TEM samples and 3D tomography/EDS/EBSD datasets.

In this talk we will explain the advantages of Xe plasma FIBS from both a physico-chemical perspective and an efficiency perspective based on the physics of how they work and their performance.

Another technology that greatly adds to the analytical power of FIB-SEMs is ToF SIMS (Time of Flight Secondary Ion Mass Spectrometry). While EDS is a useful analytical technique for elemental analysis, ToF SIMS offers increased capabilities due to lower physical limits and increased spatial resolution. We will explain how ToF SIMS works, benefits compared to EDS and how it enhances the analytical capabilities of a FIB-SEM through a more elegant integration.

Learn how Xe plasma FIB with ToF SIMS can benefit your research and produce cutting edge results by providing more detailed analyses in less time, hence giving you an even better understanding of your system.



Xe plasma FIB with ToF SIMS Seminar
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THE UNIVERSITY
OF QUEENSLAND
AUSTRALIA

Presenter: Antonin Doupal, TESCAN

Venue: The University of Queensland

Campus: St Lucia Campus

Building: AIBN building #75

Room: Level 4 meeting room

Date: Monday, 20th February 2017

Time: 10:00am – 11:00am

RSVP: seminars@axt.com.au or 02 9450 1359